

Silicon PNP Power Transistors

2SA794 2SA794A

DESCRIPTION

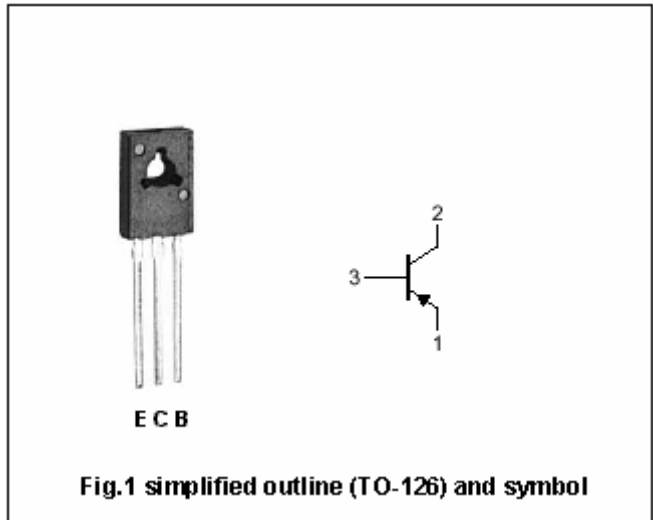
- With TO-126 package
- Complement to type 2SC1567/1567A
- High collector-emitter voltage V_{CEO}

APPLICATIONS

- For low frequency output driver
- Optimum for the driver stage of low frequency and 40W to 100W output amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA794	-100	V
		2SA794A	-120	
V_{CEO}	Collector- emitter voltage	2SA794	-100	V
		2SA794A	-120	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-0.5	A
I_{CM}	Collector current-peak		-1	A
P_C	Collector power dissipation	$T_C=25^\circ$	1.2*	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~+150	$^\circ$

*Without heat sink

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA794	I _C =-100μA ; I _B =0	-100			V
		2SA794A		-120			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-1μA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-500mA ; I _B =-50mA		-0.2	-0.4	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-500mA ; I _B =-50mA		-0.85	-1.2	V
h _{FE-1}	DC current gain		I _C =-150mA ; V _{CE} =-10V	90		220	
h _{FE-2}	DC current gain		I _C =-500mA ; V _{CE} =-5V	50			
C _{OB}	Collector output capacitance		I _E =0 ; V _{CB} =-10V;f=1MHz		20		pF
f _T	Transition frequency		V _{CB} =-10V;I _E =50mA;f=200MHz		120		MHz

◆ h_{FE-1} Classifications

Q	R
90-155	130-220

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PACKAGE OUTLINE

